Miquel Garriga

List of Publications by Year in descending order

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109137 95083 4,982 123 35 68 citations g-index h-index papers 123 123 123 4715 docs citations times ranked citing authors all docs

#	Article	IF	Citations
1	Efficient infrared sunlight absorbers based on gold-covered, inverted silicon pyramid arrays. Materials Advances, 2022, 3, 2364-2372.	2.6	2
2	Quantifying thermal transport in buried semiconductor nanostructures via cross-sectional scanning thermal microscopy. Nanoscale, 2021, 13, 10829-10836.	2.8	12
3	Photoluminescence of Boundâ€Exciton Complexes and Assignment to Shallow Defects in Methylammonium/Formamidinium Lead Iodide Mixed Crystals. Advanced Optical Materials, 2021, 9, 2001969.	3.6	11
4	Beating the Thermal Conductivity Alloy Limit Using Long-Period Compositionally Graded Si _{1–<i>x</i>} Ge <i>_x</i> Superlattices. Journal of Physical Chemistry C, 2020, 124, 19864-19872.	1.5	9
5	Phase Diagram of Methylammonium/Formamidinium Lead Iodide Perovskite Solid Solutions from Temperature-Dependent Photoluminescence and Raman Spectroscopies. Journal of Physical Chemistry C, 2020, 124, 3448-3458.	1.5	42
6	Spectroscopic ellipsometry study of FA <i>x</i> MA1â^' <i>x</i> PbI3 hybrid perovskite single crystals. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2019, 37, .	0.6	7
7	Equal Footing of Thermal Expansion and Electron–Phonon Interaction in the Temperature Dependence of Lead Halide Perovskite Band Gaps. Journal of Physical Chemistry Letters, 2019, 10, 2971-2977.	2.1	64
8	Ultrathin Semiconductor Superabsorbers from the Visible to the Nearâ€Infrared. Advanced Materials, 2018, 30, 1705876.	11.1	29
9	Localized thinning for strain concentration in suspended germanium membranes and optical method for precise thickness measurement. AIP Advances, 2018, 8, 115131.	0.6	3
10	Optical Properties of Semiconductors. Springer Series in Optical Sciences, 2018, , 89-113.	0.5	3
11	Pressure-Induced Locking of Methylammonium Cations versus Amorphization in Hybrid Lead Iodide Perovskites. Journal of Physical Chemistry C, 2018, 122, 22073-22082.	1.5	42
12	Thermal transport in epitaxial Si $<$ sub $>$ 1 \hat{a} $<$ i $>$ x $<$ ii $>$ >Ge $<$ i $><$ sub $>$ x $<$ /sub $>$ alloy nanowires with varying composition and morphology. Nanotechnology, 2017, 28, 505704.	1.3	9
13	Spectroscopic imaging ellipsometry of self-assembled SiGe/Si nanostructures. Applied Surface Science, 2017, 421, 547-552.	3.1	1
14	Evaluation of the dielectric function of colloidal Cd1 \hat{a} °xHgxTe quantum dot films by spectroscopic ellipsometry. Applied Surface Science, 2017, 421, 295-300.	3.1	6
15	Photoinduced p―to n―ype Switching in Thermoelectric Polymerâ€Carbon Nanotube Composites. Advanced Materials, 2016, 28, 2782-2789.	11.1	89
16	Growth and Characterization of Epitaxial In-plane SiGe Alloy Nanowires. Materials Today: Proceedings, 2015, 2, 548-556.	0.9	4
17	Composition and Strain Imaging of Epitaxial In-Plane SiGe Alloy Nanowires by Micro-Raman Spectroscopy. Journal of Physical Chemistry C, 2015, 119, 22154-22163.	1.5	6
18	Tailoring thermal conductivity by engineering compositional gradients in Silâ^'x Ge x superlattices. Nano Research, 2015, 8, 2833-2841.	5.8	31

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19	The dielectric tensor of monoclinic $\hat{l}\pm -3,4,9,10$ -perylene tetracarboxylic dianhydride in the visible spectral range. Thin Solid Films, 2014, 571, 420-425.	0.8	5
20	On the complex refractive index of polymer:fullerene photovoltaic blends. Thin Solid Films, 2014, 571, 371-376.	0.8	23
21	Uniaxial macroscopic alignment of conjugated polymer systems by directional crystallization during blade coating. Journal of Materials Chemistry C, 2014, 2, 3303-3310.	2.7	39
22	Using high pressure to unravel the mechanism of visible emission in amorphous Si/SiOxnanoparticles. Physical Review B, 2014, 89, .	1.1	14
23	Dependence on pressure of the refractive indices of wurtzite ZnO, GaN, and AlN. Physical Review B, 2014, 90, .	1.1	13
24	Poly(3-hexylthiophene) nanowires in porous alumina: internal structure under confinement. Soft Matter, 2014, 10, 3335.	1.2	38
25	Optical properties of ceria–zirconia epitaxial films grown from chemical solutions. Materials Chemistry and Physics, 2013, 138, 462-467.	2.0	18
26	Raman spectroscopy as a probe of molecular order, orientation, and stacking of fluorinated copperâ€phthalocyanine (F ₁₆ CuPc) thin films. Journal of Raman Spectroscopy, 2013, 44, 597-607.	1.2	11
27	Oneâ€Step Macroscopic Alignment of Conjugated Polymer Systems by Epitaxial Crystallization during Spinâ€Coating. Advanced Functional Materials, 2013, 23, 2368-2377.	7.8	73
28	Probing local strain and composition in Ge nanowires by means of tip-enhanced Raman scattering. Nanotechnology, 2013, 24, 185704.	1.3	21
29	Determination of Thermal Transition Depth Profiles in Polymer Semiconductor Films with Ellipsometry. Macromolecules, 2013, 46, 7325-7331.	2.2	26
30	Valence band structure engineering of thin SiGe/Si quantum wells for piezoresistive applications. Physica Status Solidi (B): Basic Research, 2013, 250, 760-764.	0.7	3
31	Patterned optical anisotropy in woven conjugated polymer systems. Applied Physics Letters, 2012, 101, 171907.	1.5	2
32	Influence of alloy inhomogeneities on the determination by Raman scattering of composition and strain in Si1–xGex/Si(001) layers. Journal of Applied Physics, 2012, 112, 023512.	1.1	18
33	Organic solar cells based on nanoporous P3HT obtained from self-assembled P3HT:PS templates. Journal of Materials Chemistry, 2012, 22, 20017.	6.7	35
34	Vapour printing: patterning of the optical and electrical properties of organic semiconductors in one simple step. Journal of Materials Chemistry, 2012, 22, 4519.	6.7	16
35	Surface vs bulk phase transitions in semiconducting polymer films for OPV and OLED applications. Synthetic Metals, 2012, 161, 2570-2574.	2.1	20
36	Oneâ€pot synthesis of polymer/inorganic hybrids: toward readily accessible, lowâ€loss, and highly tunable refractive index materials and patterns. Journal of Polymer Science, Part B: Polymer Physics, 2012, 50, 65-74.	2.4	32

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37	Synthesis of nanocrystalline ceria thin films by low-temperature thermal decomposition of Ce-propionate. Thin Solid Films, 2012, 520, 1949-1953.	0.8	29
38	In-Plane Epitaxial Growth of Self-Assembled Ge Nanowires on Si Substrates Patterned by a Focused Ion Beam. Crystal Growth and Design, 2011, 11, 3190-3197.	1.4	20
39	Enhanced Fano Resonance in Asymmetrical Au:Ag Heterodimers. Journal of Physical Chemistry C, 2011, 115, 6410-6414.	1.5	83
40	Real-time studies during coating and post-deposition annealing in organic semiconductors. Thin Solid Films, 2011, 519, 2678-2681.	0.8	15
41	Evidence of quantum confinement effects on interband optical transitions in Si nanocrystals. Physical Review B, 2010, 82, .	1.1	56
42	Polarized Raman study of self-assembled Ge/Si dots under hydrostatic pressure. Physica Status Solidi (B): Basic Research, 2009, 246, 482-485.	0.7	1
43	Measurement of phonon pressure coefficients for a precise determination of deformation potentials in SiGe alloys. Physica Status Solidi (B): Basic Research, 2009, 246, 548-552.	0.7	7
44	Ellipsometric study of crystallization of amorphous Ge thin films embedded in SiO2. Thin Solid Films, 2008, 516, 4277-4281.	0.8	10
45	On the determination of anisotropy in polymer thin films: A comparative study of optical techniques. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 1270-1273.	0.8	21
46	Uniaxial anisotropy of organic thin films determined by ellipsometry. Physica Status Solidi (A) Applications and Materials Science, 2008, 205, 927-930.	0.8	20
47	Ellipsometric measurements of quantum confinement effects on higher interband transitions of Ge nanocrystals. Physica Status Solidi (A) Applications and Materials Science, 2008, 205, 888-891.	0.8	4
48	Composition dependence of the phonon strain shift coefficients of SiGe alloys revisited. Applied Physics Letters, 2008, 92, .	1.5	51
49	Exciton-phonon coupling in diindenoperylene thin films. Physical Review B, 2008, 78, .	1.1	91
50	Phonon pressure coefficient as a probe of the strain status of self-assembled quantum dots. Applied Physics Letters, 2007, 91, 081914.	1.5	20
51	Raman scattering interferences as a probe of vertical coherence in multilayers of carbon-induced Ge quantum dots. Physical Review B, 2007, 76, .	1.1	8
52	Evolution of strain and composition during growth and capping of Ge quantum dots with different morphologies. Nanotechnology, 2007, 18, 475401.	1.3	15
53	SNOM Characterization of Self-Assembled Organic Nanocrystals. AIP Conference Proceedings, 2007, , .	0.3	0
54	Raman scattering of capped and uncapped carbon-induced Ge dots under hydrostatic pressure. Physica Status Solidi (B): Basic Research, 2007, 244, 76-81.	0.7	5

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55	Growth dynamics of C-induced Ge dots on Si1â^'xGex strained layers. Surface Science, 2007, 601, 2783-2786.	0.8	5
56	Spectral ellipsometry of a nanodiamond composite. Semiconductors, 2006, 40, 829-833.	0.2	3
57	Influence of Si interdiffusion on carbon-induced growth of Ge quantum dots: a strategy for tuning island density. Nanotechnology, 2006, 17, 2602-2608.	1.3	17
58	Density control on self-assembling of Ge islands using carbon-alloyed strained SiGe layers. Applied Physics Letters, 2006, 89, 101921.	1.5	18
59	Self-organization of phthalocyanines on Al2O3 (1120) in aligned and ordered films. Journal of Materials Research, 2004, 19, 2061-2067.	1.2	18
60	Optical properties of anisotropic materials: an experimental approach. Thin Solid Films, 2004, 455-456, 124-131.	0.8	19
61	Structure, morphology, and optical properties of thin films of F16CuPc grown on silicon dioxide. Organic Electronics, 2004, 5, 135-140.	1.4	36
62	The 2:1 complex of 4-aminobenzoic acid and 4,4′-bipyridylN,N′-dioxide. Acta Crystallographica Section E: Structure Reports Online, 2003, 59, o495-o497.	0.2	5
63	Spectral ellipsometry of amorphous hydrogenated carbon grown by magnetron sputtering of graphite. Semiconductors, 2003, 37, 1211-1213.	0.2	0
64	Chalcogenide glass-based rib ARROW waveguide. Journal of Non-Crystalline Solids, 2003, 326-327, 455-459.	1.5	23
65	Strong optical anisotropies of F16CuPc thin films studied by spectroscopic ellipsometry. Journal of Chemical Physics, 2003, 119, 6335-6340.	1.2	37
66	Controlled Molecular Alignment in Phthalocyanine Thin Films on Stepped Sapphire Surfaces. Advanced Functional Materials, 2002, 12, 455-460.	7.8	62
67	Optical functions of chalcopyrite CuGa x In 1-x Se 2 alloys. Applied Physics A: Materials Science and Processing, 2002, 74, 659-664.	1.1	160
68	Effect of strain and ordering on the band-gap energy of InGaP. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2002, 88, 139-142.	1.7	7
69	Anisotropic optical properties of single crystalline PTCDA studied by spectroscopic ellipsometry. Organic Electronics, 2002, 3, 23-31.	1.4	63
70	Optical transitions near the band edge in bulk CulnxGa1â^'xSe2 from ellipsometric measurements. Materials Chemistry and Physics, 2001, 70, 300-304.	2.0	35
71	Development of Zirconia Plasma Sprayed Coatings for Dental Implants and for Knee Prostheses. Key Engineering Materials, 2001, 218-220, 515-520.	0.4	1
72	Influence of tensile and compressive strain on the band gap energy of ordered InGaP. Applied Physics Letters, 2001, 79, 2758-2760.	1.5	10

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73	Optical studies of gap, hopping energies, and the Anderson-Hubbard parameter in the zigzag-chain compoundSrCuO2. Physical Review B, 2001, 63, .	1.1	20
74	Optical properties of CuAlSe2. Journal of Applied Physics, 2000, 88, 1923-1928.	1.1	29
75	Optical properties of chalcopyrite CuAlxIn1â^'xSe2 alloys. Journal of Applied Physics, 2000, 88, 5796-5801.	1.1	45
76	Caracterización estructural mediante elipsometrÃa espectral de multicapas basadas en SiO ₂ . Boletin De La Sociedad Espanola De Ceramica Y Vidrio, 2000, 39, 729-734.	0.9	0
77	Growth of Si nuclei on SiO2 for quantum dot memory applications. Microelectronic Engineering, 1999, 48, 431-434.	1.1	9
78	Ellipsometry on Very Thick Multilayer Structures. Physica Status Solidi (B): Basic Research, 1999, 215, 247-251.	0.7	9
79	Growth of Nanoscale Si Nuclei on SiO2 by Rapid Thermal Chemical Vapor Deposition. Journal of the Electrochemical Society, 1999, 146, 4219-4225.	1.3	4
80	Characterisation of complex multilayer structures using spectroscopic ellipsometry. European Physical Journal Special Topics, 1999, 09, Pr8-1195-Pr8-1202.	0.2	0
81	Doping dependence of the ellipsometric spectra of Nd2â^'xCexCuO4â^'Î' single crystals. Physica C: Superconductivity and Its Applications, 1998, 299, 41-51.	0.6	5
82	Ellipsometric characterisation of ordered Ga ^{0.5} In ^{0.5} P. Materials Science and Technology, 1998, 14, 1283-1285.	0.8	1
83	Ellipsometric measurement of the dielectric tensor of Nd2â^'xCexCuO4â^'Î'. Physical Review B, 1997, 55, 3216-3221.	1.1	9
84	Optical determination of growth variants in ordered GalnP. Solid State Communications, 1997, 101, 757-760.	0.9	8
85	Determination of the dielectric tensor in anisotropic materials. Applied Physics Letters, 1995, 67, 596-598.	1.5	16
86	Spin orientation by optical pumping in InxGa1â^'xAs/AlAs multiple quantum wells. Solid State Communications, 1994, 91, 703-707.	0.9	0
87	Temperature dependence of the dielectric function and interband critical points of AlAs obtained on an MBE grown layer. Thin Solid Films, 1993, 233, 122-125.	0.8	16
88	Temperature dependence of the dielectric function and the interband critical-point parameters of GaP. Thin Solid Films, 1993, 233, 185-188.	0.8	14
89	Quantum well lasers with InAs monolayers in the active region grown at low temperature by atomic layer molecular beam epitaxy. Journal of Crystal Growth, 1993, 127, 46-49.	0.7	2
90	Growth and characterization of A1As/GaInAs multiple quantum wells. Journal of Crystal Growth, 1993, 127, 611-615.	0.7	3

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91	Structural and optical characterization of alternately strained GaAs/GaP/GaAs/InP superlattices grown by atomic layer molecular beam epitaxy. Journal of Crystal Growth, 1993, 127, 623-626.	0.7	1
92	Temperature dependence of the refractive index of crystalline germanium-silicon alloys. Applied Physics A: Materials Science and Processing, 1993, 56, 259-261.	1.1	9
93	Temperature dependence of the dielectric function and the interband critical-point parameters of GaP. Physical Review B, 1993, 48, 7915-7929.	1.1	79
94	Optical characterization of InAs monolayer structures grown on (113)A and (001) GaAs substrates. Applied Physics Letters, 1993, 62, 1000-1002.	1.5	15
95	Quantum well laser with single InAs monolayer in active region. Electronics Letters, 1992, 28, 935-937.	0.5	10
96	Xâ€ray characterization of InAs laser structures grown by molecular beam epitaxy. Journal of Applied Physics, 1992, 72, 2528-2530.	1.1	1
97	Optical characterization of AlAs/GalnAs multiple quantum wells. Superlattices and Microstructures, 1992, 12, 207-210.	1.4	2
98	Interband transitions in YBa2Cu3O7. Physica C: Superconductivity and Its Applications, 1992, 192, 473-480.	0.6	16
99	Temperature dependence of the dielectric function and the interband critical-point parameters of GaSb. Physical Review B, 1991, 43, 4349-4360.	1.1	77
100	Optical anisotropy in the Pb2Sr2(Y, Ca)Cu3O8+ \hat{l} superconductor. Physica C: Superconductivity and Its Applications, 1991, 174, 377-382.	0.6	8
101	Temperature dependence of the dielectric function and the interband critical-point parameters of AlxGalâ^xAs. Physical Review B, 1991, 43, 11950-11965.	1.1	66
102	Resonant Raman scattering in thePb2Sr2(Y,Ca)Cu3O8+δsuperconductor. Physical Review B, 1990, 41, 830-833.	1.1	16
103	Ultrafast initial relaxation of hot electrons and holes in tetrahedral semiconductors via deformation potential interaction: Theory and experiment. Applied Physics Letters, 1990, 57, 2838-2840.	1.5	19
104	Spectral ellipsometry of semiconductors and semiconductor structures., 1990, 1286, 111.		1
105	E2interband transitions inAlxGa1â^'xAs alloys. Physical Review B, 1990, 41, 2959-2965.	1.1	36
106	Optical response of Bi2Sr2CaCu2O8 superconductors. Solid State Communications, 1990, 73, 127-130.	0.9	19
107	Anisotropy of the dielectric function in YBa 2Cu 3O6. Physical Review B, 1989, 40, 7368-7371.	1.1	57
108	Resonant Raman scattering in short-period (Si)n/(Ge)msuperlattices. Physical Review B, 1989, 40, 1361-1364.	1.1	38

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109	Ellipsometric and reflectance studies of GaAs/AlAs superlattices. Applied Physics A: Solids and Surfaces, 1989, 49, 407-412.	1.4	18
110	Ellipsometric measurements of high-Tc compounds. Journal of the Optical Society of America B: Optical Physics, 1989, 6, 470.	0.9	41
111	Optical spectra of SixGe1â°'xalloys. Journal of Applied Physics, 1989, 65, 2827-2832.	1.1	245
112	Effects of oxygen deficiency on the optical spectra of YBa2Cu3O7â^'x. Solid State Communications, 1988, 66, 1231-1235.	0.9	54
113	Optical response of MBa2CuZ3O7–8-type materials. Physica C: Superconductivity and Its Applications, 1988, 153-155, 643-644.	0.6	33
114	Temperature dependence of optical excitations in MBa2Cu3O6 (M = Y,Sm). Solid State Communications, 1988, 67, 589-592.	0.9	49
115	Ellipsometric spectra of YBa2Cu3O7 in the 1.7 – 5.3 eV range. Solid State Communications, 1988, 66, 1071-1075.	0.9	26
116	Interband Transitions in Ultrathin GaAs-AlAs Superlattices. Physical Review Letters, 1988, 61, 1643-1646.	2.9	42
117	Temperature dependence of the interband critical-point parameters of InP. Physical Review B, 1987, 36, 4813-4820.	1.1	213
118	Interband critical points of GaAs and their temperature dependence. Physical Review B, 1987, 35, 9174-9189.	1.1	786
119	Interband transitions of thin-layer GaAs/AlAs superlattices. Physical Review B, 1987, 36, 3254-3258.	1.1	86
120	Optical properties of AlAs. Solid State Communications, 1987, 61, 157-160.	0.9	59
121	Temperature dependence of the dielectric function and interband critical points in silicon. Physical Review B, 1987, 36, 4821-4830.	1.1	717
122	POSITION AND CHARACTER (Ɖ OR X) OF ENERGY STATES IN SHORT-PERIOD (GaAs)m(AlAs)n SUPERLATTICES. Journal De Physique Colloque, 1987, 48, C5-495-C5-498.	0.2	25
123	Temperature dependence of the dielectric function and the interband critical points of CdSe. Physical Review B, 1986, 34, 2458-2469.	1.1	176